

connection facilitated by the conductive adhesive. Such metallization would likely be applied during the latter stages of wafer fabrication, after completion of the final topside passivation.

Please replace the paragraph beginning on page 4, line 7 with the following amended paragraph:

Referring to FIGS. 2A and 2B. Die 200 has an arrangement of bond pads 210. In applying an embodiment of the present invention, during the design and layout process, the circuit 205 may be arranged to have interior pads 205 connected to ground in the core area of the die, as well as the typical bond pads ~~215~~ 210. The interior pads 205 may be laid out to make optimum use of the core area. The interior pads 205 ~~locations~~ may be located at the center (as illustrated in FIG. 2B) or be offset from the center at appropriately defined areas.

Please replace the paragraph beginning on page 4, line 13 with the following amended paragraph:

Referring to FIG. 3, in an example embodiment, on a device die 300, the grounding pads 325 are located near the bond pads 310. Layer 327 is an insulating mask that exposes the grounding pads 325 but protects the die 300 from unintended ground connections after the application of a conductive adhesive 449 such as shown in ~~FIG. 4A~~ FIG. 5A.

Change(s) applied to document, /T.N✓
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Please replace the paragraph beginning on page 5, line ¹⁶~~15~~ with the following amended paragraph:

Referring to FIG. 8, in an example embodiment, in place of grounding pads 515, a conductive grid ~~530-630~~ may be laid across the die and be coupled to bonding pads defined as ground. The defining of grounded bonding pads may be part of the device's design process. The second die ~~520-620~~ on its underside may then be bonded with